MBR2080CTG, MBR2090CTG, MBR20100CTG

Switch-mode Power Rectifiers

This series uses the Schottky Barrier principle with a platinum barrier metal. These state−of−the−art devices have the following features:

Features

- 20 A Total (10 A Per Diode Leg)
- Guard−Ring for Stress Protection
- Low Forward Voltage
- 175°C Operating Junction Temperature
- Epoxy Meets UL 94 V−0 @ 0.125 in
- Low Power Loss/High Efficiency
- High Surge Capacity
- Low Stored Charge Majority Carrier Conduction
- Shipped 50 units per plastic tube
- These Devices are Pb−Free and are RoHS Compliant*

Mechanical Characteristics:

- Case: Epoxy, Molded
- Weight: 1.9 grams (approximately)
- Finish: All External Surfaces Corrosion Resistant and Terminal Leads are Readily Solderable
- Lead Temperature for Soldering Purposes: 260°C Max. for 10 Seconds

*For additional information on our Pb−Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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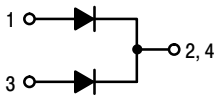
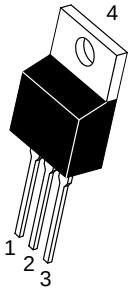
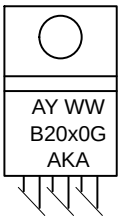
SCHOTTKY BARRIER RECTIFIERS 20 AMPERES 80−100 VOLTS





TO−220
CASE 221A
STYLE 6

MARKING DIAGRAM



A	= Assembly Location
Y	= Year
WW	= Work Week
B20x0	= Device Code
x	= 8, 9 or 10
G	= Pb−Free Device
AKA	= Polarity Designator

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 2 of this data sheet.

MAXIMUM RATINGS (Per Diode Leg)

Rating	Symbol	MBR			Unit
		2080CT	2090CT	20100CT	
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V_{RRM} V_{RWM} V_R	80	90	100	V
Average Rectified Forward Current (Rated V_R) T_C = 133°C	$I_{F(AV)}$	10			A
Peak Repetitive Forward Current (Rated V_R, Square Wave, 20 kHz) T_C = 133°C	I_{FRM}	20			A
Nonrepetitive Peak Surge Current (Surge applied at rated load conditions halfwave, single phase, 60 Hz)	I_{FSM}	150			A
Peak Repetitive Reverse Surge Current (2.0 μs, 1.0 kHz)	I_{RRM}	0.5			A
Operating Junction Temperature (Note 1)	T_J	−65 to +175			°C
Storage Temperature	T_{stg}	−65 to +175			°C
Voltage Rate of Change (Rated V_R)	dv/dt	10,000			V/μs

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. The heat generated must be less than the thermal conductivity from Junction−to−Ambient: $dP_D/dT_J < 1/R_{\theta JA}$.

THERMAL CHARACTERISTICS

Characteristic	Symbol	Value	Unit
Maximum Thermal Resistance Junction−to−Case Junction−to−Ambient	$R_{\theta JC}$ $R_{\theta JA}$	2.0 60	°C/W

ELECTRICAL CHARACTERISTICS (Per Diode Leg)

Characteristic	Symbol	Value	Unit
Maximum Instantaneous Forward Voltage (Note 2) (i_F = 10 Amps, T_C = 125°C) (i_F = 10 Amps, T_C = 25°C) (i_F = 20 Amps, T_C = 125°C) (i_F = 20 Amps, T_C = 25°C)	v_F	 0.75 0.85 0.85 0.95	V
Maximum Instantaneous Reverse Current (Note 2) (Rated dc Voltage, T_C = 125°C) (Rated dc Voltage, T_C = 25°C)	i_R	 6.0 0.1	mA

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

2. Pulse Test: Pulse Width = 300 μs, Duty Cycle ≤ 2.0%.

ORDERING INFORMATION

Device	Package	Shipping
MBR2080CTG	TO−220 (Pb−Free)	50 Units / Rail
MBR2090CTG	TO−220 (Pb−Free)	50 Units / Rail
MBR20100CTG	TO−220 (Pb−Free)	50 Units / Rail

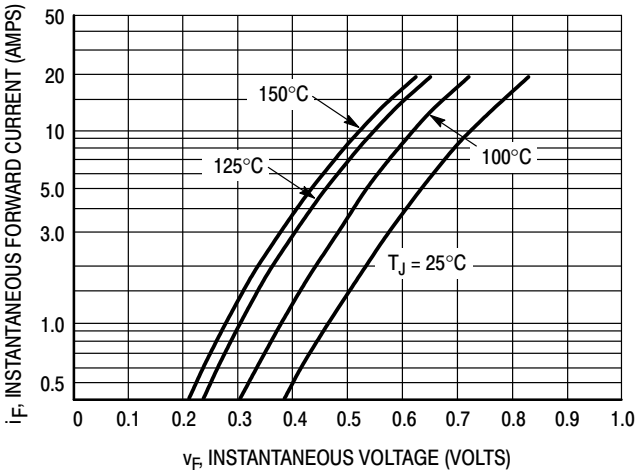


Figure 1. Typical Forward Voltage Per Diode

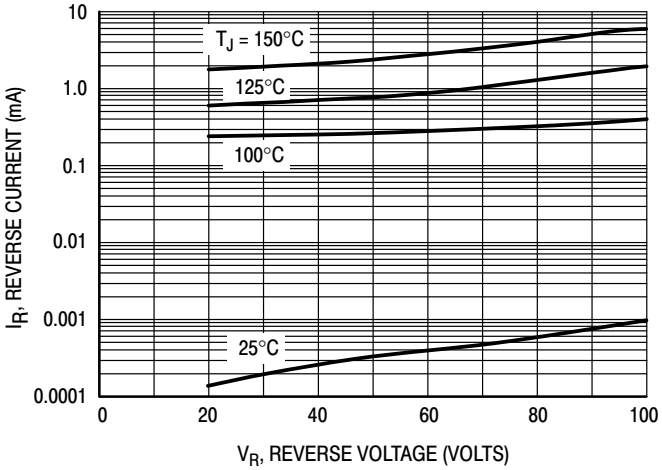


Figure 2. Typical Reverse Current Per Diode

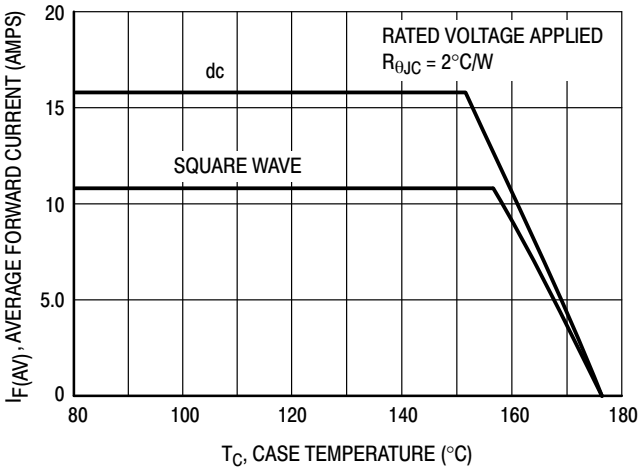


Figure 3. Typical Current Derating, Case, Per Leg

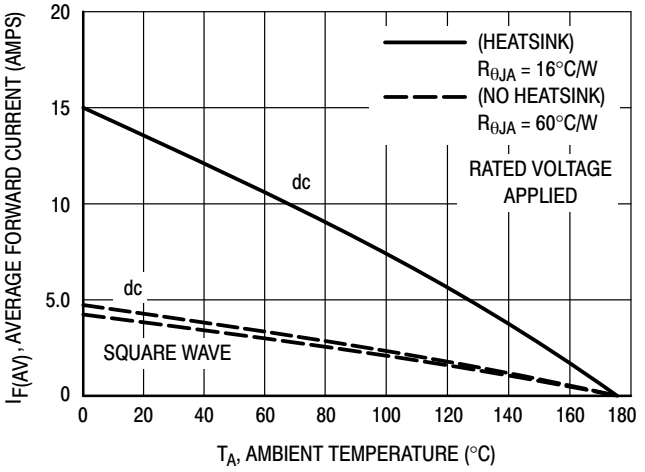


Figure 4. Typical Current Derating, Ambient, Per Leg

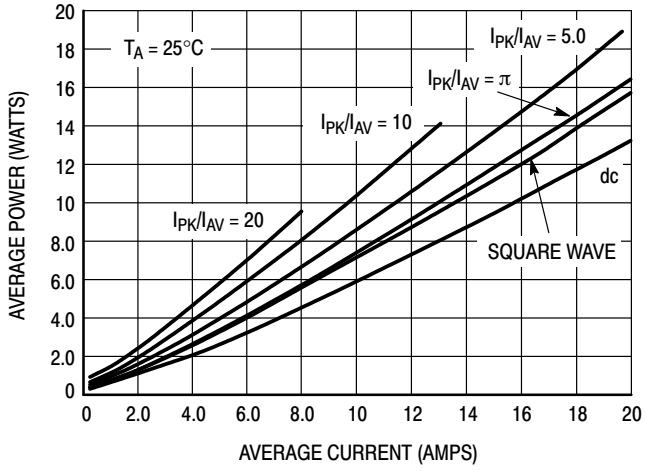
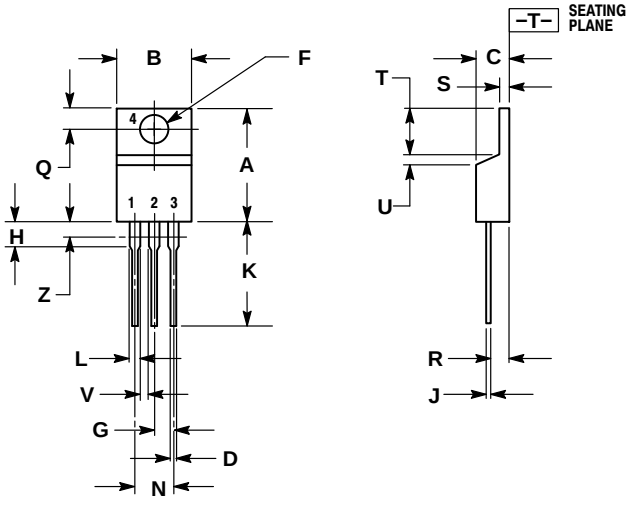


Figure 5. Average Power Dissipation and Average Current

PACKAGE DIMENSIONS

TO−220
CASE 221A−09
ISSUE AH



NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. DIMENSION Z DEFINES A ZONE WHERE ALL BODY AND LEAD IRREGULARITIES ARE ALLOWED.

	INCHES		MILLIMETERS	
DIM	MIN	MAX	MIN	MAX
A	0.570	0.620	14.48	15.75
B	0.380	0.415	9.66	10.53
C	0.160	0.190	4.07	4.83
D	0.025	0.038	0.64	0.96
F	0.142	0.161	3.61	4.09
G	0.095	0.105	2.42	2.66
H	0.110	0.161	2.80	4.10
J	0.014	0.024	0.36	0.61
K	0.500	0.562	12.70	14.27
L	0.045	0.060	1.15	1.52
N	0.190	0.210	4.83	5.33
Q	0.100	0.120	2.54	3.04
R	0.080	0.110	2.04	2.79
S	0.045	0.055	1.15	1.39
T	0.235	0.255	5.97	6.47
U	0.000	0.050	0.00	1.27
V	0.045	---	1.15	---
Z	---	0.080	---	2.04

STYLE 6:
PIN 1. ANODE
2. CATHODE
3. ANODE
4. CATHODE

PUBLICATION ORDERING INFORMATION

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